13003BS

Preliminary

NPN SILICON TRANSISTOR

NPN SILICON BIPOLAR TRANSISTORS FOR LOW FREQUENCY AMPLIFICATION

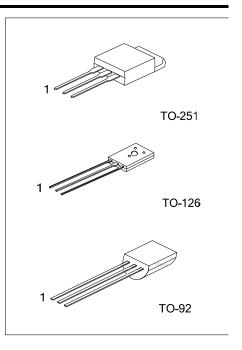
DESCRIPTION

The UTC 13003BS is a silicon NPN power switching transistor; it uses UTC's advanced technology to provide customers high collector-base breakdown voltage, low reverse leakage current and high reliability, etc.

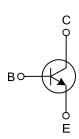
The UTC 13003BS is suitable for electronic ballast power switch circuit and the compact electronic energy-saving light.

FEATURES

- * High collector-base breakdown voltage
- * Low reverse leakage current
- * High reliability



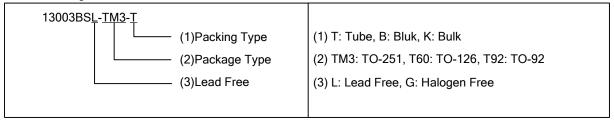
EQUIVALENT CIRCUIT



ORDERING INFORMATION

Ordering Number		Daakana	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package 1 2		2	3	Packing	
13003BSL-TM3-T	13003BSG-TM3-T	TO-251	В	С	Е	Tube	
13003BSL-T60-K	13003BSG-T60-K	TO-126	В	С	Е	Bulk	
13003BSL-T92-B	13003BSG-T92-B	TO-92	В	С	Е	Tape Box	
13003BSI -T92-K	13003BSG-T92-K	TO-92	В	С	F	Bulk	

Note: Pin Assignment: B: Base C: Collector E: Emitter



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■ MARKING INFORMATION

PACKAGE	MARKING
TO-251	UTC 13003BS ☐ → P: Halogen Free Lot Code ← → Data Code
TO-126	UTC DDD Data Code 13003BSD L: Lead Free 1 P: Halogen Free
TO-92	UTC 13003BS L: Lead Free P: Halogen Free Data Code

■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
ollector-Base Voltage		V_{CBO}	800	V
Collector-Emitter Voltage		V_{CEO}	450	V
Emitter-Base Voltage	-Base Voltage		9	V
Callagtar Current	Continuous	Ic	2	Α
Collector Current	Peak	I _{CM}	4	Α
Base Current	Continuous	I _B	1	Α
Base Current	Peak	I _{BM}	2	Α
Power Dissipation (T _C =25°C)	TO-251		10	W
	TO-126	P_{D}	20	W
	TO-92]	1	W
Junction Temperature		TJ	150	°C
Storage Temperature Range	re Range T _{STG} -55~+150		°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT	
Junction to Ambient	TO-251		90		
	TO-126	θ_{JA}	100	°C/W	
	TO-92		150		
Junction to Case	TO-251		12.5		
	TO-126	θ_{JC}	7.5	°C/W	
	TO-92		100		

■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =1mA, I _E =0	800			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	450			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =1mA, I _C =0	9			V
Collector Cut-Off Current	I _{CBO}	V_{CB} =800V, I_{E} =0			0.1	mA
Collector-Emitter Cut-Off Current	I _{CEO}	V _{CE} =450V, I _B =0			0.1	mA
Emitter-Base Cut-Off Current	I _{EBO}	$V_{EB}=9V$, $I_{C}=0$			0.1	mA
DC Current Gain (Note)	h_{FE}	V_{CE} =5V, I_{C} =0.2mA	20		35	
	h _{FE1} / h _{FE2}	h _{FE1} : V _{CE} =5V, I _C =5mA	0.75			
Low current and high current h _{FE2} h _{FE1} ratio		h_{FE2} : V_{CE} =5 V , I_{C} =0.2 A	0.75			
Collector-Emitter Saturation Voltage (Note)	$V_{CE(SAT)}$	I _C =0.5A, I _B =0.1A			0.8	V
Base-Emitter Saturation Voltage (Note)	$V_{BE(SAT)}$	I _C =0.5A, I _B =0.1A			1.5	V
Storage Time	t _S		2		5	μs
Rise Time	t_R	UI9600, I _C =0.25A			2	μs
Fall Time	t_{F}				2	μs
Transition Frequency	f_T	V _{CE} =10V, I _C =0.1A, f=1MHz	5			MHz

Note: Pulse test, pulse width tp≤300µs, Duty cycle≤2%.

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